

WHAT IS CLAIMED IS:

1. A method of depositing a thin metal-oxide film having a uniform thickness of about 200 Å or less, comprising:
 - 5 a) delivering one or more liquid precursors to a vaporizer;
 - b) vaporizing the one or more liquid precursors;
 - c) delivering the vaporized precursors to a deposition chamber to deposit a film on a substrate; and
 - d) repeating steps (a)-(c) at least one time.
- 10 2. The method of Claim 1, wherein at least a first precursor flow rate is used in a first step and a second precursor flow rate is used in a second step.
3. The method of Claim 2, wherein said first precursor flow rate and said second precursor flow rate are different from one another.
- 15 4. The method of Claim 2, wherein said first precursor flow rate and said second precursor flow rate are the same.
5. The method of Claim 1, wherein at least a first mixture of precursor gases is used in a first step and a second mixture of precursor gases is used in a second step.
6. The method of Claim 5, wherein said first mixture of precursor gases and said second mixture of precursor gases are different from one another.
- 20 7. The method of Claim 5, wherein said first mixture of precursor gases and said second mixture of precursor gases are the same.
8. The method of Claim 5, wherein said first mixture of precursor gases and said second mixture of precursor gases comprises BST and oxygen.

9. The method of Claim 1, wherein said process is halted for a predetermined waiting period prior to carrying out step (d).

10. The method of Claim 9, wherein said predetermined waiting period is between about 10 seconds and about 300 seconds.

5 11. A film prepared by the method of Claim 1.

12. A DRAM capacitor comprising the film of Claim 11.